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م\ قبول نشر

نهديكم أطيب التحيات: تدارست هينة التحرير بحثكم الموسوم :-

# STUDY THE EFFECT OF MAGNET IC FIELD ON THE PROPERTIES OF SILVER THIN FILMS PREPARED BY . DC SPUTTERING

والمقدم للنشر في مجله القادسية للعلوم الصرفة وبعد الاطلاع على اراء المقيمين واستنادا الى ما قررته هيئه التحرير في جلستها الرابعة المنعقدة في ١٦ /٢٠١٧ ما يلى :-

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# STUDY THE EFFECT OF MAGNET IC FIELD ON THE PROPERTIES OF SILVER THIN FILMS PREPARED BY DC SPUTTERING .

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**ABSTRACT:** Silver thin films by Dc sputtering method on glass substrate for different deposition times (10,30 and 60)sec have been prepared and deposited. The thicknesses of Ag thin films measured by using an optical interferometer method employing He-Ne laser (632.8)nm wavelength. Thin films thicknesses without magnetic field was (84,89 and 94)nm while with magnetic field was(127,269 and 290)nm for same times. Structure and Optical properties have been analyzed by using XRD and UV-V spectroscopy and XRD analysis show that thin films were face centered cubic structure. Absorption and Transmittance spectra of silver thin films were recorded in the wavelength range between 300nm to1100nm. High absorption coefficient of silver thin films determined from the analysis of absorption spectra . The electrical properties show the resistivity inversely proportional with silver thin films thickness.

KEYWORD: Structure and Optical properties, Ag thin films, DC sputtering,

# **1-INTRODUCTION**

The electrical and structural properties of thin metal films can be effected by a large number of parameters such as time ,surface, thickness and other parameter. A composition of two or more thin film phases of metal can improve the structural ,electrical and optical properties . The wide uses of silver thin films is in knowledge of microelectronics, capacitors and transistors, because of their excellent physical and electrical properties[1,2]. Silver has many interesting attributes, like excellent high frequently virtues, highest electrical conductivity , low resistivity, and a rather high melting [3] .the inset of Ag particles into thin films cans enhancement film conductivity[4]. Silver is one of the best conducting metals and widely used in the modern world for electrical conduction in multiple industries and applications, including light-emitting diodes (LED) and flat-panel displays (FPD)[5].Ag thin films have also been widely applied in optical applications, mainly due to their high transparency and neutral color in the visible range, they also exhibit extremely high reflectivity near infrared (IR) and IR of spectrum[6]. These properties make Ag thin films ideal candidates for low-thermal-emissivity coatings on glass panels, leading to energy-efficient windows for residential and commercial buildings . For the lest twenty years, low- thermal-emissivity coatings have motivated an intense research activated to improve the growth mode and optical properties of Ag thin films ,ultimately leading to substantial energy savings<sup>[7]</sup>. Silver thin films had been prepared by several techniques such as DC and RF magnetron sputtering, chemical vapor deposition(CVD), pulsed laser deposition(PLD) , ion-assisted deposition and electron beam evaporation [8] .In the present investigation ,DC magnetron sputtering was used to prepare Ag films and study its effects on thickness films.

Magnetron sputtering is one of well developed method for thin film fabrication ,its extensive use in industrial application depends on the ability of obtaining high quality films with high value of deposition rate [9]. F.Penning was the first Physicist suggested to use sputtering magnetron for the film deposition as early as 1935, it is important not only for industrial application but also for scientific and technology research [10]. In a basic sputtering process, a target

(or source) material to be deposition onto substrate, is bombarded by energetic ions typically inert gas ions such as Argon  $(Ar^{+})$ . The strong collisions of these inert gas ions with target atoms causes the removal of target atoms which condense on the substrate as a thin film of stoichiometry similar to that of target material [11] . Magnetron sputtering systems produce a strong magnetic field near the target area which causes the mobile electrons to spiral along magnetic flux lines near the target . This arrangement confines the plasma in near the target area without causing the damage to the thin films being formed on the substrate and maintains on thickness uniformity of deposition thin film [12].

# **2- EXPERIMENTAL**

## 2-1 Materials and method :

In the first step, Ag films were deposition on glass substrates by using DC magnetron sputtering using SPC-12 system compact plasma Sputtering coater origin (MTR Corporation, CA 94804, USA ). and by addition coil to produce variable magnetic field and permanent magnetic field, the sputtering target was of the metal silver with purity of 99.9%. the deposition chamber has been evacuated to base pressure of  $4 \times 10^{-2}$ After introduction mmHg. of the sputtering gas (Ar 99.9%) into the chamber ,the deposition pressure was  $8 \times 10^{-2}$  mmHg and the deposition time for all films were (10,30 and 60) sec ,the distance between the target and substrate was (4cm). The thicknesses of Ag films was(127,269 and 290) nm . In the second step, we used the method of plasma sputtering without magnetic field at the same deposition conditions for deposition Ag films, where the thicknesses of thin

films was (84,89 and 94) nm in this method. The crystal structures of thin films analyzed by X-ray diffraction (XRD) using the device carries the following specifications (TYPE: XRD-6000. SHIMADZU, **JAPANESE** ORIGIN, TARGET: Cu K $\alpha$ ,  $\lambda = (1.5406)$ Å, Speed: (5) deg / min, voltage: (40) KV, current: (30) MA, range ( $2\theta$ ): 30-100 deg The optical properties of Ag thin films analyzed by using UV-Vis spectra .The electrical properties of the prepared thin films were studied .

## 2-2Thin films thickness measurements:

The thickness of Ag thin films were measured by using an optical interferometer method employing He-Ne laser (632.8)nm wavelength with incident angle  $45^{\circ}$ .



Figure.(1): (a) sputtering system and (b) the electrical circuit of the coil .

sample condition	Base pressure (mmHg)	Work pressure (mmHg)	Voltage (V)	Current (mA)	Deposition time (sec)	Thickness (nm)
without	$4 \times 10^{-2}$	8×10 <sup>-2</sup>	216	15	10,30,60	84 ,89,94
M.F						
with M.F	4×10 <sup>-2</sup>	8×10 <sup>-2</sup>	189	20	10,30,60	127,269,269
(100)Gauss						

Table 1.Deposition parameters of Ag thin films .

# **3- RESULT AND DISCUSSION**

## **3-1 Structure properties :**

Figure 2, shows the X-ray diffraction pattern of Ag thin films deposition on glass substrates and different with thicknesses (t=269 nm, t=290 nm). the polycrystalline Ag films can be observed and the peak namely the (111), (200), (220), (311) illustrates in fig.2, according to ICDD numbered card (00-004-0783), cubic type the (111) Ag peak intensity was larger than that of the other peaks because the (111) direction to Ag films has lowest surface energy, and we calculate the lattice constant of the Ag films prepared for installation cube from equation (1) [13].

$$d_{hkl} = \frac{a}{\sqrt{h^2 + k^2 + l^2}} \qquad \dots (1)$$

Where:(hkl) are Miller coefficients, (a) is lattice constant and  $d_{hkl}$  is the distance between the plans(hkl). The average crystallite size to the prevailing direction (111) was calculated from equation(1), while the average grain size calculated from the following equation [14].

$$D_{av} = \frac{0.09\,\lambda}{B\,COS\theta} \qquad \dots (2)$$

Where  $D_{av}$ : is the grain size,  $\lambda$  is the wavelength of cu-k $\alpha$  radiation used( $\lambda = 1.5406$  Å),  $\beta$ : is full width half maximum intensity (FWHM) and  $\theta$  is the Bragg angle.

We notice that the average grain size leads to increases thickness of films and

also leads to increase the surface roughness and increase the homogeneity of the film as shown in Table(2).This result corresponds with research [8] .



Figure (2): The XRD patter of as deposition Ag films on glass substrate :( a) without magnetic field and (b) within magnetic field.

sample Ag	2θ(deg)	2θ(deg) ICDD	d(A)	hkl	$a_0(A^0)$	The Average grain size (nm)
sample a	38.80	38.11	2.309	111	4.0875	144.976
t=94nm	44.13	44.27	2.044	200		
	64.28	64.42	1.445	220		
	77.44	77.47	1.231	311		
sample b	38.11	38.11	2.359	111		
t=290nm	44.27	44.27	2.0438	200		
	64.42	64.42	1.445	220		
	77.47	77.47	1.230	311		

#### **3-2** Optical properties:

The optical measurement of the prepared films carried out using UV-Vis-NIR (300-1100) nm Spectroscope and the spectral dependence of the transmittance (T) and absorption(A) for all Ag films. The absorption spectra of Ag thin films as a function of wavelength ranging from(300-1100)nm are shows in figure (3). The films show surface resonance peak observed at 450 nm . The absorption increase with deposition time and thin films thickness . Figure (4) Shows the transmittance spectra at same wavelength to1100nm . The ranging from 300nm transmittance shows opposite behavior of optical absorption and transmittance decreases at the short wavelength until to reaches the lowest value of wavelength(400)nm and proportional with wavelength, thickness and time. Optical reflectance, optical constants includes absorption Coefficient ( $\alpha$ ) as a function of wavelength calculated by using absorption and transmittance spectra.



Figure(3) UV-Vis Absorption of Ag thin films (a) without magnetic field and (b) within magnetic field



Figure(4) UV-Vis transmittance of Ag thin films (a) without magnetic field and (b) within magnetic field.

# **3-2-1 Calculation of reflectivity:**

The reflectivity of silver Ag films was calculated with and without magnetic field from absorption (A) spectra and transmittance(T) form equation (3) [15] .

Figure(5) ,shows the reflectivity film as a function of wavelength with and without magnetic field , we can observe that the values of reflectivity rise until to reach their highest value at short wavelength(400)nm and then begin to decrease with increasing wavelength.



Figure(5) reflectivity spectra of Ag thin films (a) without magnetic field and (b) within magnetic field.

# **3-2-2** Calculation of absorption coefficient (α):

The absorption coefficient of silver films calculated from the following equation [16]:

α=2.303 A/t ....(4)

where A is the absorption and t is thin film thickness in (nm) unit.

Figure(6) shows absorption coefficient as a function of wavelength for the samples with different deposition times and thicknesses. Absorption coefficient increases at short wavelength until reach highest peak at (400), than to the decrease with wavelength The absorption coefficient decreases gradually with thin film thickness and time for some thin films . High absorption coefficient of silver thin films (about  $10^4 \ cm^{-1}$ ).





Figure (6): Absorption coefficient of Ag thin films (a) without magnetic field and (b) within magnetic field

#### **3-3 Electrical properties :**

The electrical properties of Ag thin metal films with different thicknesses of Ag measured by using two points prope directly connected to the avometer, where the resistance between the two propes is measured and then the electrical conductivity calculated from the following equations[17] :

$$R = \rho \frac{L}{Wt} \qquad \dots (5)$$
$$\sigma = \frac{1}{\rho} \qquad \dots (6)$$

Where R is resistance( $\Omega$ ), w is width of thin film(cm), t is thickness of thin

film(cm),  $\rho$  is the electrical resistivity ( $\Omega$  .m) and  $\sigma$  is the electrical conductivity  $(\Omega.m)^{-1}$ .

Figure (7a) and (7b) show the dependency of the Ag films resistance on thickness. So, the Ag thin films resistivity decreases with increasing Ag films thickness . This result agrees with research [1] . While the electrical conductivity will increasing with thin films thickness.



figure (7) :(a) resistanc e and (b) electrical conductivity

#### **4-CONCLUSION**

The XRD results show that Ag films polycrystalline structure with have characteristic peaks of Ag and have face centered cubic structure. The optical showed absorption properties that coefficient increased with the increasing wavelength and the presence of absorption peaks above (400)nm . The electrical results show that the resistance decrease with thin films thickness and the electrical

conductivity increasing with thin films thickness.

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# دراسة تأثير المجال المغناطيسي على خواص أغشية الفضة الرقيقة المحضرة بطريقة الترذيذ بالتيار المستمر

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#### الخلاصة

تم تحضير اغشية الفضة الرقيقة بطريقة الترذيذ بالتيار لمستمر و المرسبة على قواعد من الزجاج الازمنة مختلف (عام 30, 20, 20, 20) . تم قياس سمك اغشية الفضة الرقيقة بطريقة التداخل البصري والمتضمنة الليزر المهليوم –نيون ذات طول موجي (632.8nm) , وكان سمك الاغشية المحضرة بوجود وعدم وجود مجال معناطيسي على التوالي (632.8nm) , وكان سمك الاغشية المحضرة بوجود وعدم وجود مجال معناطيسي على التوالي (632.8nm) , وكان سمك الاغشية المحضرة الرقيقة بطريقة التداخل البصري والمتضمنة الليزر معنا وليون ذات طول موجي (632.8nm) , وكان سمك الاغشية المحضرة بوجود وعدم وجود مجال معناطيسي على التوالي (632.8nm) , وكان سمك الاغشية المحضرة بوجود وعدم وجود مجال معناطيسي على التوالي (72,269,290 ) , وكان سمك والاغشية المحضرة بوجود وعدم وجود مجال معناطيسي على التوالي (10,00 ) , وكان سمك الاغشية المحضرة بوجود وعدم وجود مجال معناطيسي على التوالي (10,00 ) , وكان سمك معناطيسي على الخواص التركيبية والبصرية والمصرية والمعن والمعنية والمعروبية والفينية والفينية والمعروبية والمعروبية والمعروبية والفينية والمعروبية والفينية في مدى طول موجي بين (1001-300) , وتم تحديد معامل الامتصاص العالي الاغشية الفينية الويقة من تحليل أطياف الامتصاصية ويبلغ حوالي وتم تحديد معامل الامتصاص العالي الاغشية بأن المقاومة تقل بزيادة سمك الاغشية الرقيقة .

الكلمات المفتاحية : الخواص التركيبية والبصرية , اغشية الفضة الرقيقة , الترذيذ بالتيار المستمر .